

BCR8CS-12LB

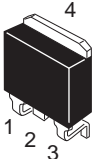

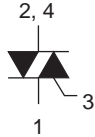
Triac
Medium Power Use

R07DS0223EJ0400
(Previous: REJ03G0468-0300)
Rev.4.00
Dec 14, 2010

Features

- $I_{T(RMS)}$: 8 A
- V_{DRM} : 600 V
- I_{FGT} , I_{RGT} , $I_{RGT III}$: 30 mA (20 mA)^{Note6}
- The product guaranteed maximum junction temperature of 150°C
- Non-Insulated Type
- Planar Passivation Type

Outline

RENESAS Package code: PRSS0004AE-B (Package name: LDK(S)-(1))	RENESAS Package code: PRSS0004AB-A (Package name: TO-220S)
	
	
1. T ₁ Terminal 2. T ₂ Terminal 3. Gate Terminal 4. T ₂ Terminal	

Applications

Solid state relay, hybrid IC

Maximum Ratings

Parameter	Symbol	Voltage class	Unit
		12	
Repetitive peak off-state voltage ^{Note1}	V_{DRM}	600	V
Non-repetitive peak off-state voltage ^{Note1}	V_{DSM}	720	V

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_{T(RMS)}$	8	A	Commercial frequency, sine full wave 360° conduction, $T_c = 130^{\circ}\text{C}$ ^{Note3}
Surge on-state current	I_{TSM}	80	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I^2t for fusing	I^2t	26	A ² s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P_{GM}	5	W	
Average gate power dissipation	$P_{G(AV)}$	0.5	W	
Peak gate voltage	V_{GM}	10	V	
Peak gate current	I_{GM}	2	A	
Junction temperature	T_j	- 40 to +150	°C	
Storage temperature	T_{stg}	- 40 to +150	°C	
Mass	—	1.3	g	Typical value

Notes: 1. Gate open.

Electrical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak off-state current	I_{DRM}	—	—	2.0	mA	$T_j = 150^\circ\text{C}$, V_{DRM} applied
On-state voltage	V_{TM}	—	—	1.5	V	$T_c = 25^\circ\text{C}$, $I_{TM} = 12\text{ A}$, Instantaneous measurement
Gate trigger voltage ^{Note2}	I	V_{FGTI}	—	—	1.5	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $R_L = 6\ \Omega$, $R_G = 330\ \Omega$
	II	V_{RGTI}	—	—	1.5	
	III	V_{RGTIII}	—	—	1.5	
Gate trigger current ^{Note2}	I	I_{FGTI}	—	—	30^{Note6}	$T_j = 25^\circ\text{C}$, $V_D = 6\text{ V}$, $R_L = 6\ \Omega$, $R_G = 330\ \Omega$
	II	I_{RGTI}	—	—	30^{Note6}	
	III	I_{RGTIII}	—	—	30^{Note6}	
Gate non-trigger voltage	V_{GD}	0.2/0.1	—	—	V	$T_j = 125^\circ\text{C}/150^\circ\text{C}$, $V_D = 1/2 V_{DRM}$
Thermal resistance	$R_{th(j-c)}$	—	—	2.0	$^\circ\text{C}/\text{W}$	Junction to case ^{Note3 Note4}
Critical-rate of rise of off-state commutating voltage ^{Note5}	$(dv/dt)_c$	10/1	—	—	$\text{V}/\mu\text{s}$	$T_j = 125^\circ\text{C}/150^\circ\text{C}$

Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. Case temperature is measured on the T_2 tab.

4. The contact thermal resistance $R_{th(c-f)}$ in case of greasing is $1.0^\circ\text{C}/\text{W}$.

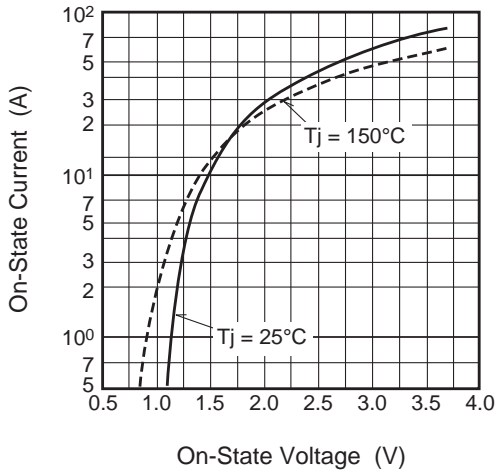
5. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

6. High sensitivity ($I_{GT} \leq 20\text{mA}$) is also available. (I_{GT} item: 1)

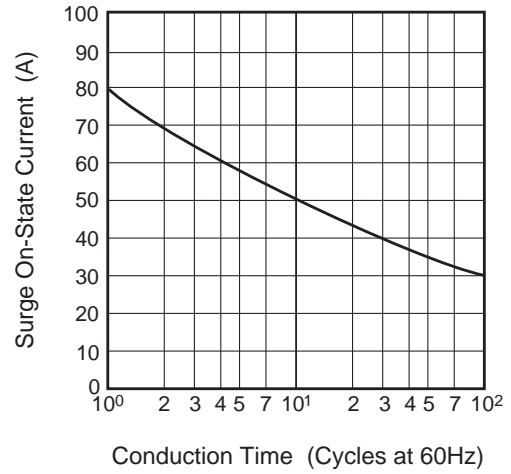
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature $T_j = 125^\circ\text{C}/150^\circ\text{C}$ 2. Rate of decay of on-state commutating current $(di/dt)_c = -4.0\text{ A/ms}$ 3. Peak off-state voltage $V_D = 400\text{ V}$	

Performance Curves

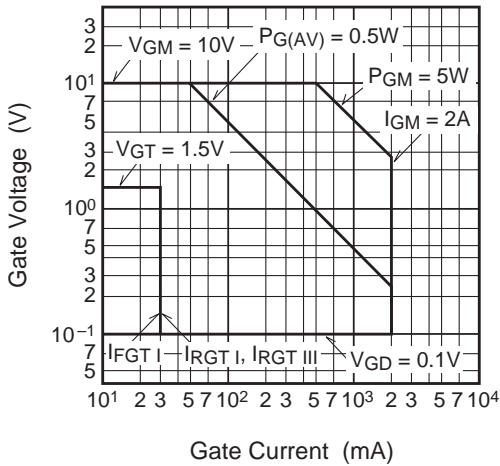
Maximum On-State Characteristics



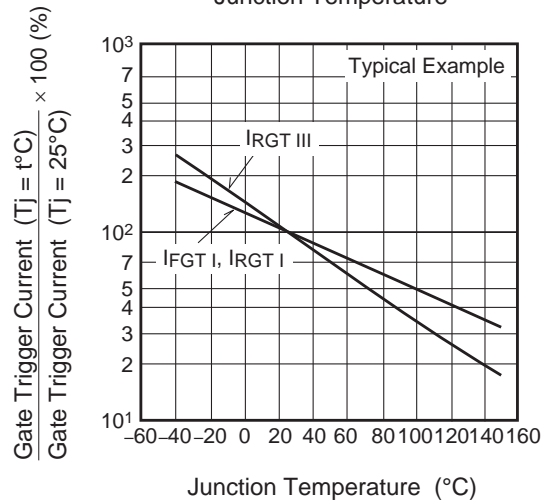
Rated Surge On-State Current



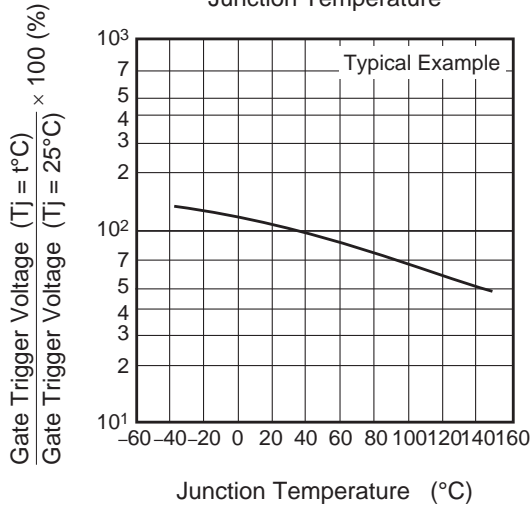
Gate Characteristics (I, II and III)



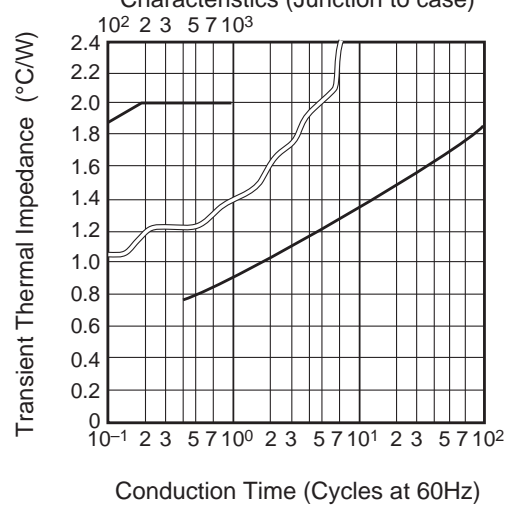
Gate Trigger Current vs. Junction Temperature



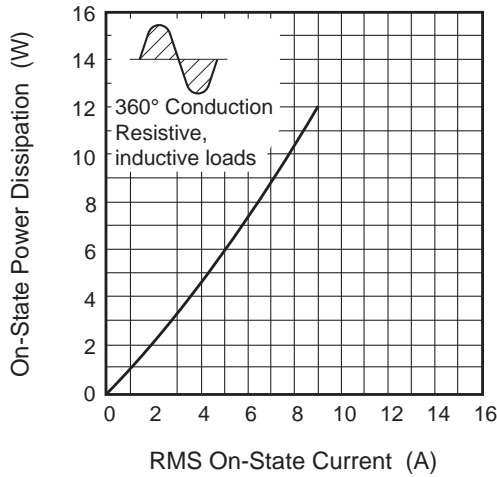
Gate Trigger Voltage vs. Junction Temperature



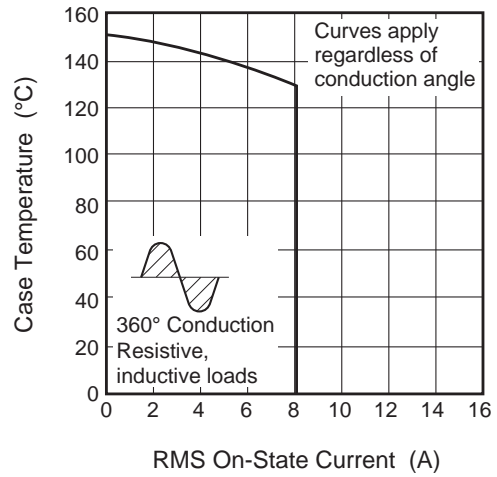
Maximum Transient Thermal Impedance Characteristics (Junction to case)



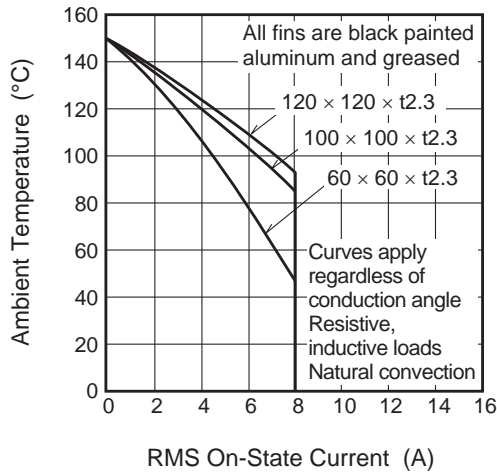
Maximum On-State Power Dissipation



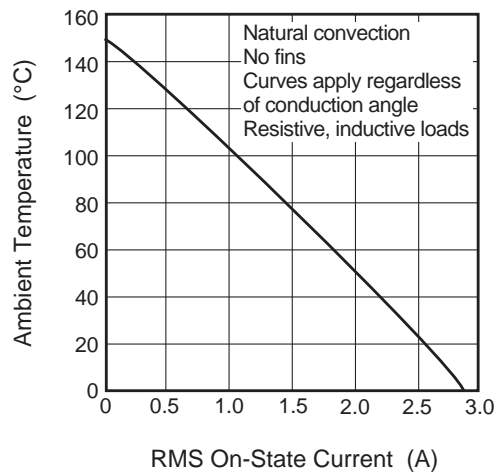
Allowable Case Temperature vs. RMS On-State Current



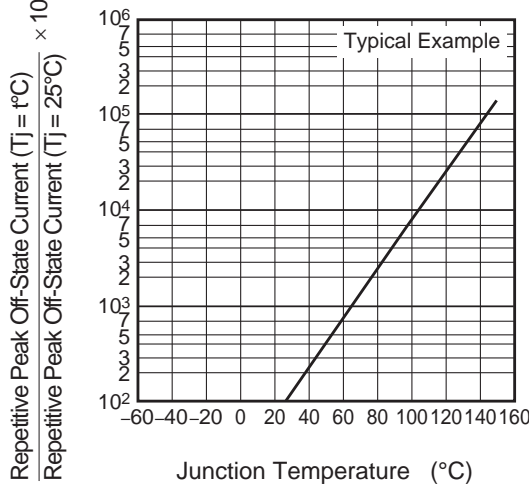
Allowable Ambient Temperature vs. RMS On-State Current



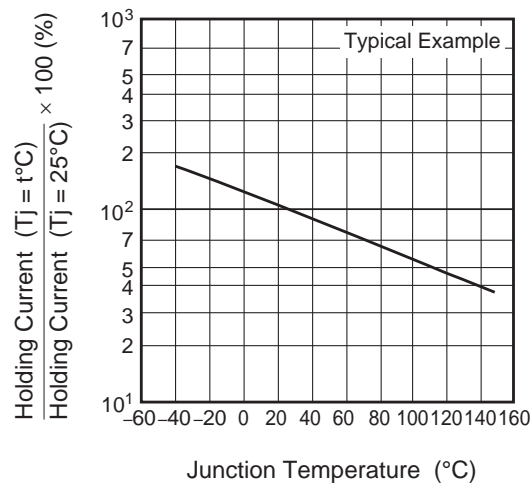
Allowable Ambient Temperature vs. RMS On-State Current



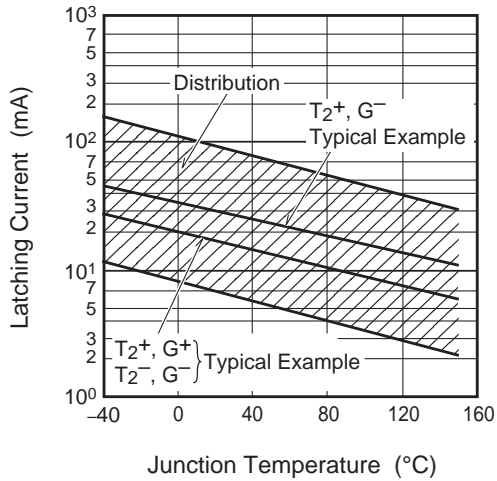
Repetitive Peak Off-State Current vs. Junction Temperature



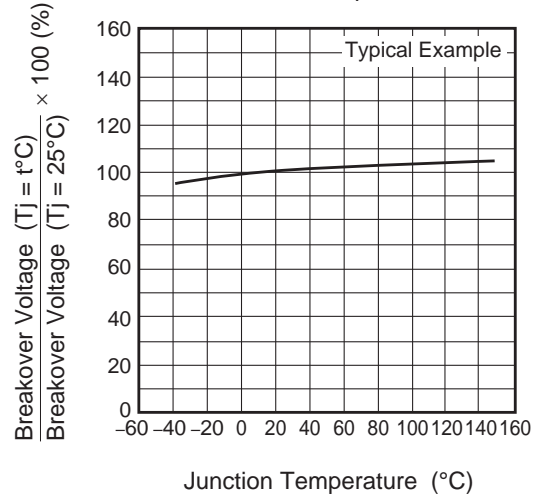
Holding Current vs. Junction Temperature



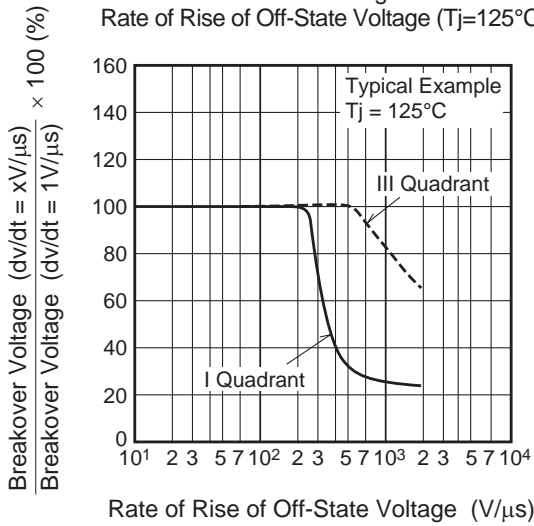
Latching Current vs. Junction Temperature



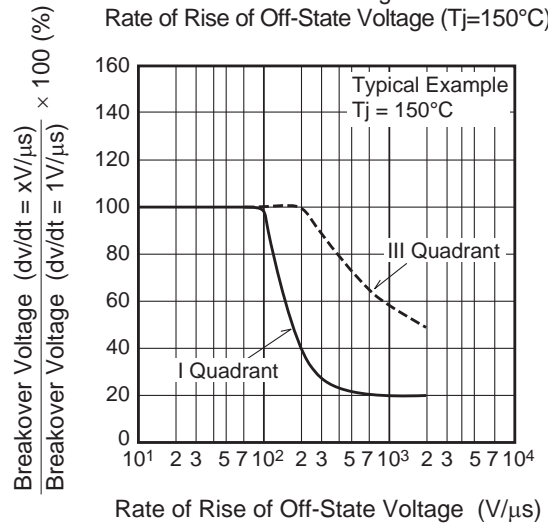
Breakover Voltage vs. Junction Temperature



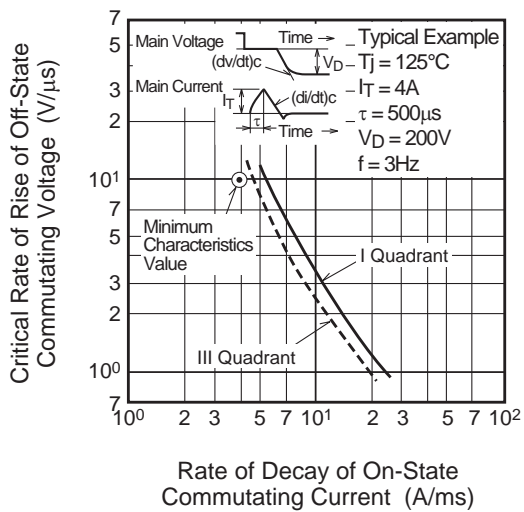
Breakover Voltage vs. Rate of Rise of Off-State Voltage (Tj=125°C)



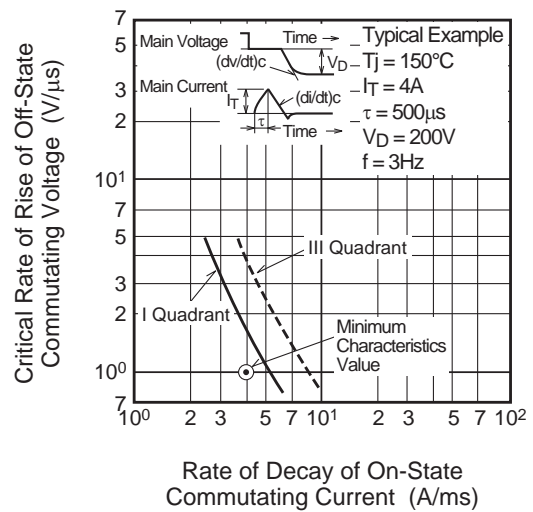
Breakover Voltage vs. Rate of Rise of Off-State Voltage (Tj=150°C)



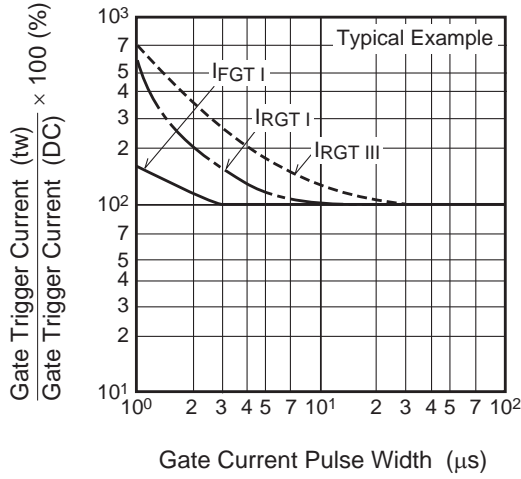
Commutation Characteristics (Tj=125°C)



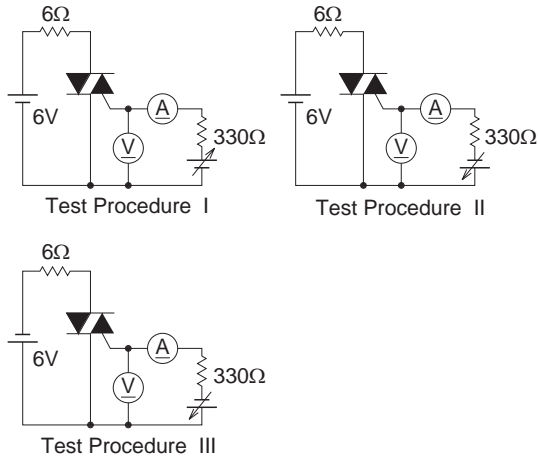
Commutation Characteristics (Tj=150°C)



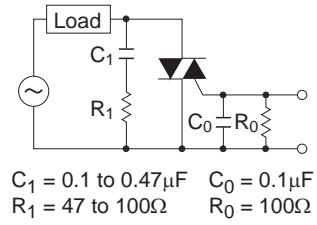
Gate Trigger Current vs. Gate Current Pulse Width



Gate Trigger Characteristics Test Circuits



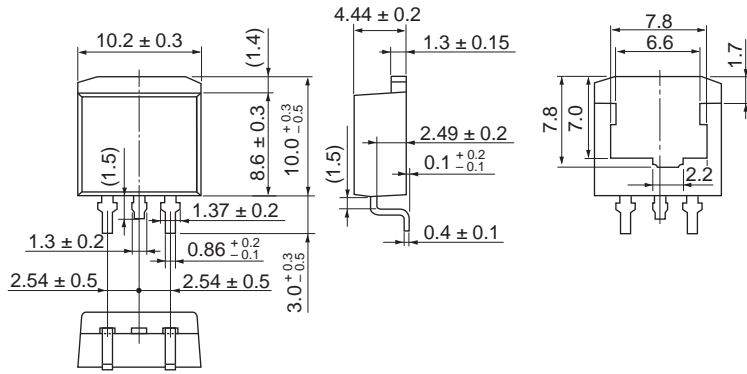
Recommended Circuit Values Around The Triac



Package Dimensions

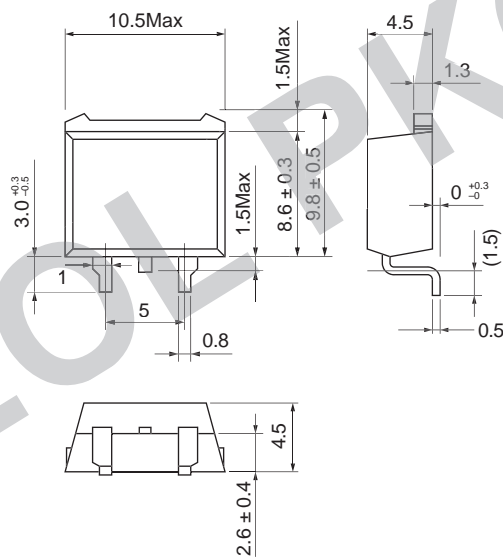
Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
LDBPAK(S)-(1)	SC-83	PRSS0004AE-B	LDBPAK(S)-(1) / LDBPAK(S)-(1)V	1.30g

Unit: mm



Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
TO-220S	SC-83	PRSS0004AB-A	TO-220S	1.2g

Unit: mm



Ordering Information

Orderable Part Number	Packing	Quantity	Remark
BCR8CS-12LB#B00	Tube	50 pcs.	—
BCR8CS-12LB-T11#B00	Embossed Tape	1000 pcs.	Taping direction "T1"

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